



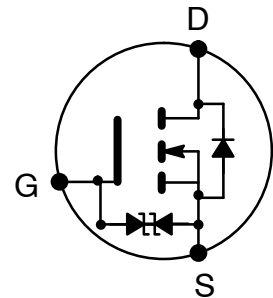
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## NTE2926 MOSFET N-Ch, Enhancement Mode High Speed Switch TO3PN Type Package

**Features:**

- Good Frequency Characteristic
- High Speed Switching
- Wide Area of Safe Operation
- Enhancement Mode
- Good Complementary Characteristics
- Equipped with Gate Protection Diodes
- Suitable for Audio Power Amplifier



**Absolute Maximum Ratings:**

Drain-Source Voltage, $V_{DSX}$ .....	160V
Gate-Source Voltage, $V_{GSS}$ .....	$\pm 15$
Drain Current, $I_D$ .....	7A
Body-to-Drain Diode Reverse Drain Current, $I_{DR}$ .....	7A
Channel Dissipation ( $T_C = +25^\circ\text{C}$ ), $P_{ch}$ .....	100W
Channel Temperature, $T_{ch}$ .....	$+150^\circ\text{C}$
Storage Temperature Range, $T_{stg}$ .....	$-55^\circ$ to $+150^\circ\text{C}$

**Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSX}$	$V_{GS} = -10\text{V}, I_D = 10\text{mA}$	160	-	-	V
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	$V_{DS} = 0\text{V}, I_G = \pm 100\mu\text{A}$	$\pm 15$	-	-	V
Gate-Source Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10\text{V}, I_D = 100\text{mA}$	0.15	-	1.45	V
Drain-Source Saturation Voltage	$V_{DS(sat)}$	$V_{GD} = 0\text{V}, I_D = 7\text{A}, \text{Note 1}$	-	-	12	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}, I_D = 3\text{A}, \text{Note 1}$	0.7	1.0	1.4	S
Input Capacitance	$C_{iss}$	$V_{GS} = -5\text{V}, V_{DS} = 10\text{V}, f = 1\text{MHz}$	-	600	-	pF
Output Capacitance	$C_{oss}$		-	350	-	pF
Reverse Transfer Capacitance	$C_{rss}$		-	10	-	pF
Turn-On Time	$t_{on}$	$V_{DD} = 20\text{V}, I_D = 4\text{A}$	-	180	-	ns
Turn-Off Time	$t_{off}$		-	60	-	ns

Note 1. Pulse test.

